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NXP Semiconductors/Freescale Semiconductor, Inc. BT139X-600E,127

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BT139X-600E

4Q Triac 1 May 2015

Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT186A "full pack" plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching. This sensitive gate "series E" triac is intended for gate triggering by low power drivers and microcontrollers.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Isolated package
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Table 1. Qu	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	-	155	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 38$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	16	A
Static charac	teristics	·				
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	4	10	mA







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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-P-T1
2	T2	main terminal 2		sym051
3	G	gate		
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

6. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BT139X-600E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A



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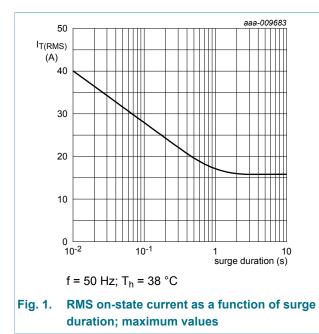
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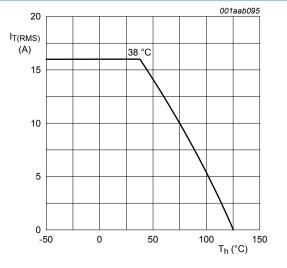
Limiting values 7.

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 38 °C; <u>Fig. 1; Fig. 2;</u> <u>Fig. 3</u>	-	16	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	155	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	170	A
l ² t	I2t for fusing	t _p = 10 ms; SIN	-	120	A ² s
dl _T /dt	rate of rise of on-state current	I _G = 20 mA; T2+ G+	-	50	A/µs
		I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 50 mA; T2- G+	-	10	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C







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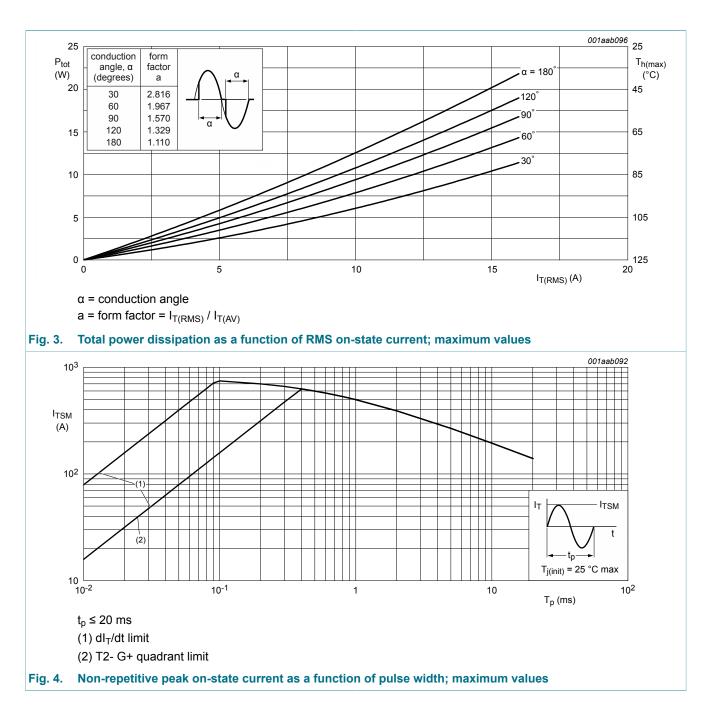
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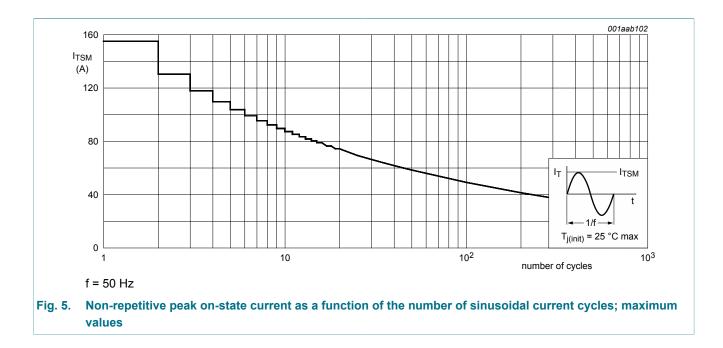




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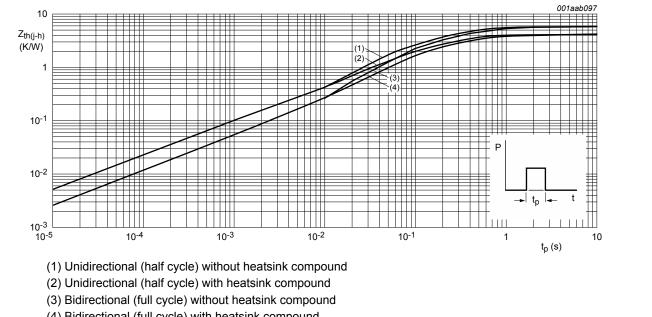
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8. Thermal characteristics

Table 5. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	full or half cycle with heatsink compound; Fig. 6	-	-	4	K/W
	heatsink	full or half cycle without heatsink compound; Fig. 6	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (4) Bidirectional (full cycle) with heatsink compound
- Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

9. Isolation characteristics

Table 6. Isola	ation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF



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10. Characteristics

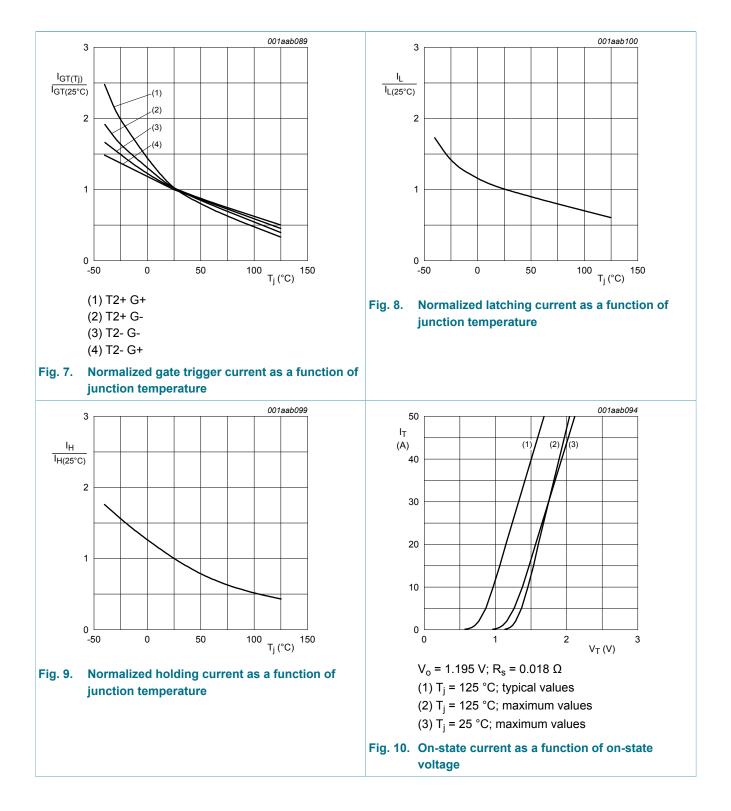
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	I				
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	4	10	mA
		V_D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	5	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	11	25	mA
L	latching current	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G+};$ $\text{T}_j = 25 \text{ °C}; \text{ Fig. 8}$	-	3.2	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; <u>Fig. 8</u>	-	16	40	mA
		V_D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	4	30	mA
		V_D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; Fig. 8	-	5.5	40	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	4	45	mA
VT	on-state voltage	I _T = 20 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·	l	1		
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	I _{TM} = 20 A; V _D = 600 V; I _G = 0.1 A; dI _G / dt = 5 A/μs	-	2	-	μs



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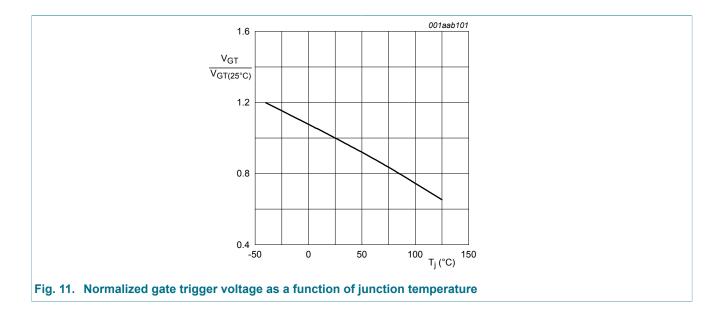




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11. Package outline

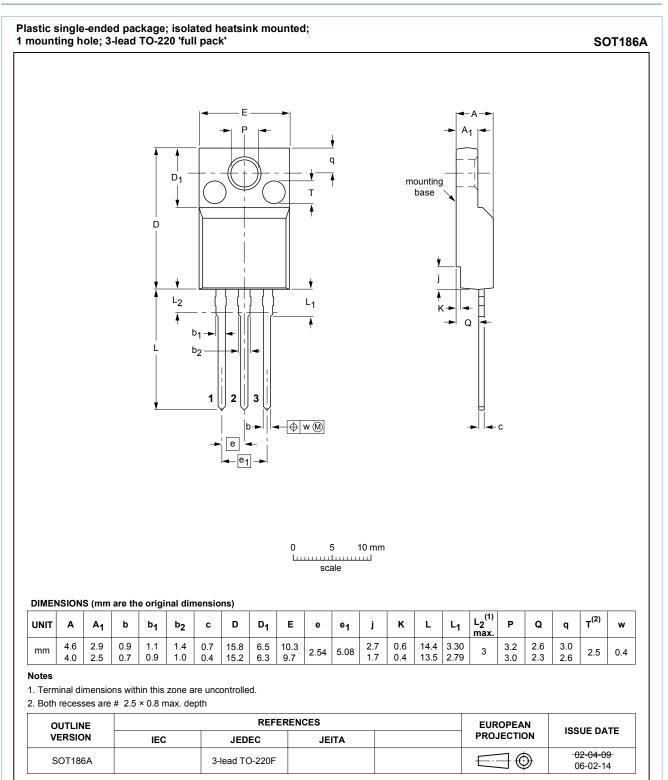


Fig. 12. Package outline TO-220F (SOT186A)

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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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